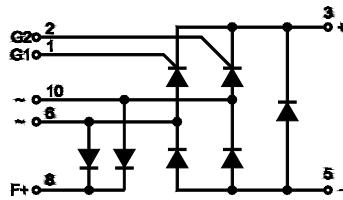


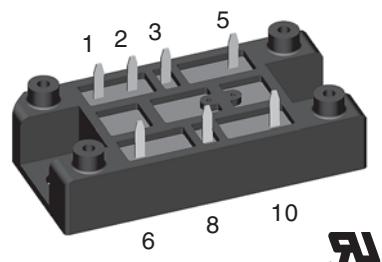
Half Controlled Single Phase Rectifier Bridge

Including Freewheeling Diode and Field Diodes

V_{RSM}	V_{RRM}	Type
V_{DSM}	V_{DRM}	
V	V	
900	800	VHFD 29-08io1
1300	1200	VHFD 29-12io1
1700	1600	VHFD 29-16io1



$V_{RRM} = 800\text{-}1600 \text{ V}$
 $I_{dAVM} = 32 \text{ A}$



Bridge and Freewheeling Diode

Symbol	Conditions	Maximum Ratings		
I_{dAV}	$T_H = 85^\circ\text{C}$, module	28	A	
I_{dAVM}^*	module	32	A	
I_{FRMS}, I_{TRMS}	per leg	25	A	
I_{FSM}, I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0 \text{ V}$	300 330	A A	
	$T_{VJ} = T_{VJM}$ $V_R = 0 \text{ V}$	270 300	A A	
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0 \text{ V}$	440 455	A^2s A^2s	
	$T_{VJ} = T_{VJM}$ $V_R = 0 \text{ V}$	365 370	A^2s A^2s	
$(di/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C}$ $f = 50 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$, $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	repetitive, $I_T = 50 \text{ A}$ non repetitive, $I_T = 0.5 I_{dAV}$	150 500	$\text{A}/\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{(v)im}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)		1000	$\text{V}/\mu\text{s}$
V_{RGM}			10	V
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = 0.5 I_{dAVM}$	$t_p = 30 \mu\text{s}$ $t_p = 500 \mu\text{s}$ $t_p = 10 \text{ ms}$	≤ 10 ≤ 5 ≤ 1	W
P_{GAVM}			0.5	W
T_{VJ}			-40...+125	$^\circ\text{C}$
T_{VJM}			125	$^\circ\text{C}$
T_{stg}			-40...+125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$ $t = 1 \text{ s}$	3000 3600	V_\sim
d_s	Creep distance on surface		12.7	mm
d_A	Strike distance in air		9.4	mm
a	Max. allowable acceleration		50	m/s^2
M_d	Mounting torque (M5) (10-32 UNF)		2-2.5 18-22	Nm lb.in.
Weight			35	g

Features

- Package with DCB ceramic base plate
- Isolation voltage 3600 V \sim
- Planar passivated chips
- Blocking voltage up to 1600 V
- Low forward voltage drop
- Leads suitable for PC board soldering
- UL registered E 72873

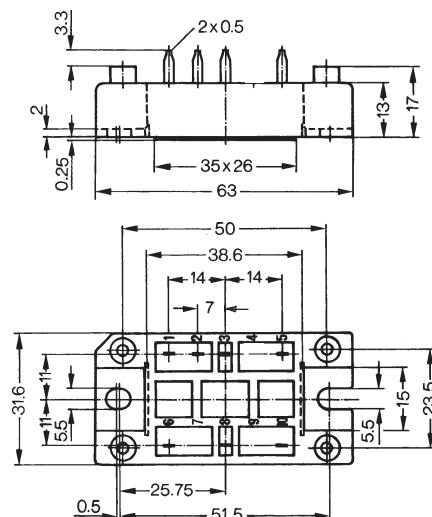
Applications

- Supply for DC power equipment
- DC motor control

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Symbol	Conditions	Characteristic Values		
I_R, I_D	$V_R = V_{RRM}; V_D = V_{DRM}$ $T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ C$	≤ 5	mA	
		≤ 0.3	mA	
V_T, V_F	$I_T, I_F = 45 A; T_{VJ} = 25^\circ C$	≤ 1.6	V	
V_{TO}	For power-loss calculations only ($T_{VJ} = 125^\circ C$)	0.9	V	
r_T		15	mΩ	
V_{GT}	$V_D = 6 V;$ $T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$	≤ 1.0	V	
		≤ 1.2	V	
I_{GT}	$V_D = 6 V;$ $T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$ $T_{VJ} = 125^\circ C$	≤ 65	mA	
		≤ 80	mA	
		≤ 50	mA	
V_{GD}	$T_{VJ} = T_{VJM};$	$V_D = 2/3 V_{DRM}$	≤ 0.2	V
I_{GD}	$T_{VJ} = T_{VJM};$	$V_D = 2/3 V_{DRM}$	≤ 5	mA
I_L	$I_G = 0.3 A; t_G = 30 \mu s;$ $di_G/dt = 0.3 A/\mu s;$ $T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$ $T_{VJ} = 125^\circ C$	≤ 150	mA	
		≤ 200	mA	
		≤ 100	mA	
I_H	$T_{VJ} = 25^\circ C; V_D = 6 V; R_{GK} = \infty$	≤ 100	mA	
t_{gd}	$T_{VJ} = 25^\circ C; V_D = 0.5 V_{DRM}$ $I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$	≤ 2	μs	
t_q	$T_{VJ} = 125^\circ C, I_T = 15 A, t_p = 300 \mu s, V_R = 100 V$	typ.	150	μs
Q_r	$di/dt = -10 A/\mu s, dv/dt = 20 V/\mu s, V_D = 2/3 V_{DRM}$	75	μC	
R_{thJC}	per thyristor (diode); DC current	1.4	K/W	
	per module	0.35	K/W	
R_{thJH}	per thyristor (diode); DC current	2.0	K/W	
	per module	0.5	K/W	

Field Diodes

Symbol	Conditions	Maximum Ratings		
I_{FAV}	$T_H = 85^\circ C$, per Diode	4	A	
I_{FAVM}	per diode	4	A	
I_{FRMS}	per diode	6	A	
I_{FSM}	$T_{VJ} = 45^\circ C; V_R = 0 V$ $t = 10 ms (50 Hz), sine$ $t = 8.3 ms (60 Hz), sine$	100	A	
		110	A	
	$T_{VJ} = T_{VJM} V_R = 0 V$ $t = 10 ms (50 Hz), sine$ $t = 8.3 ms (60 Hz), sine$	85	A	
		94	A	
I^2t	$T_{VJ} = 45^\circ C V_R = 0 V$ $t = 10 ms (50 Hz), sine$ $t = 8.3 ms (60 Hz), sine$	50	A ² s	
		50	A ² s	
	$T_{VJ} = T_{VJM} V_R = 0 V$ $t = 10 ms (50 Hz), sine$ $t = 8.3 ms (60 Hz), sine$	36	A ² s	
		37	A ² s	
I_R	$V_R = V_{RRM}$	1	mA	
	$T_{VJ} = T_{VJM}$	0.15	mA	
	$T_{VJ} = 25^\circ C$			
V_F	$I_F = 21 A; T_{VJ} = 25^\circ C$	1.83	V	
V_{TO}	For power-loss calculations only ($T_{VJ} = 125^\circ C$)	0.9	V	
r_T		50	mΩ	
R_{thJC}	per diode; DC current	4.4	K/W	
R_{thJH}	per diode; DC current	5.2	K/W	

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

* for resistive load

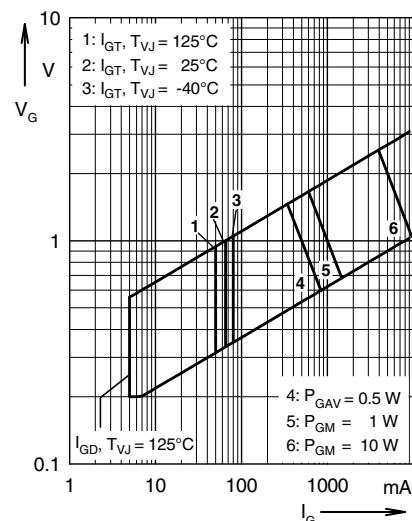


Fig. 1 Gate trigger range

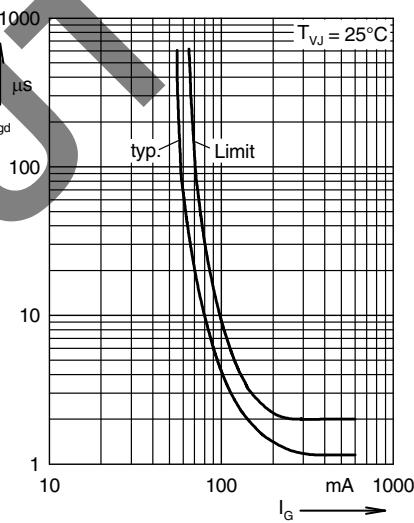


Fig. 2 Gate controlled delay time t_{gd}

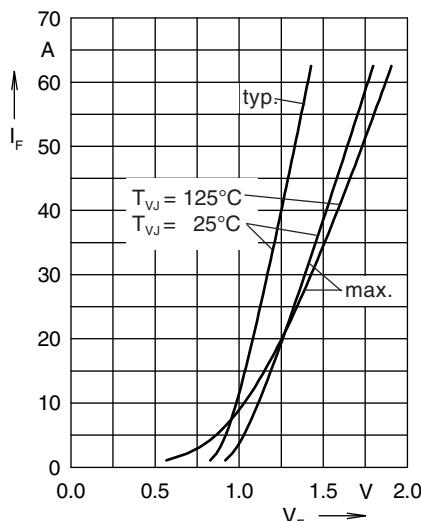


Fig. 3 Forward current vs. voltage drop per diode

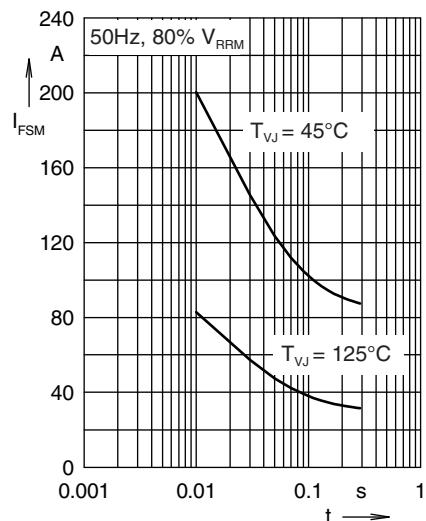


Fig. 4 Surge overload current

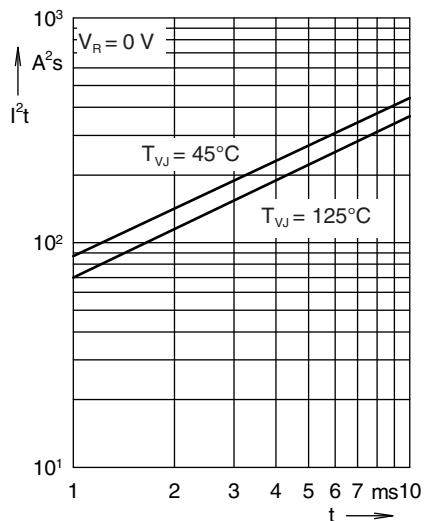
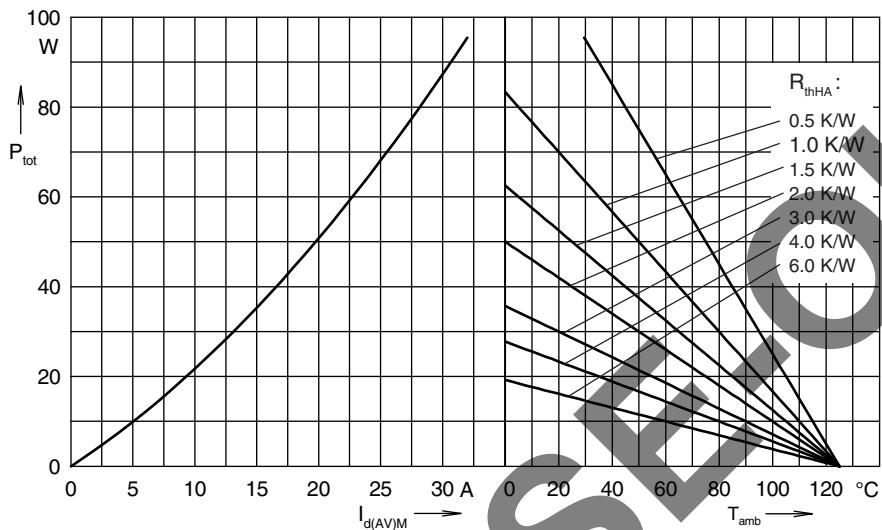
Fig. 5 I^2t versus time per diode

Fig. 6 Power dissipation vs. direct output current and ambient temperature

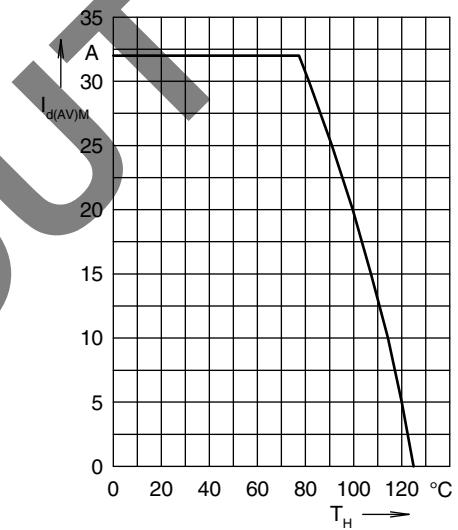


Fig. 7 Max. forward current vs. heatsink temperature

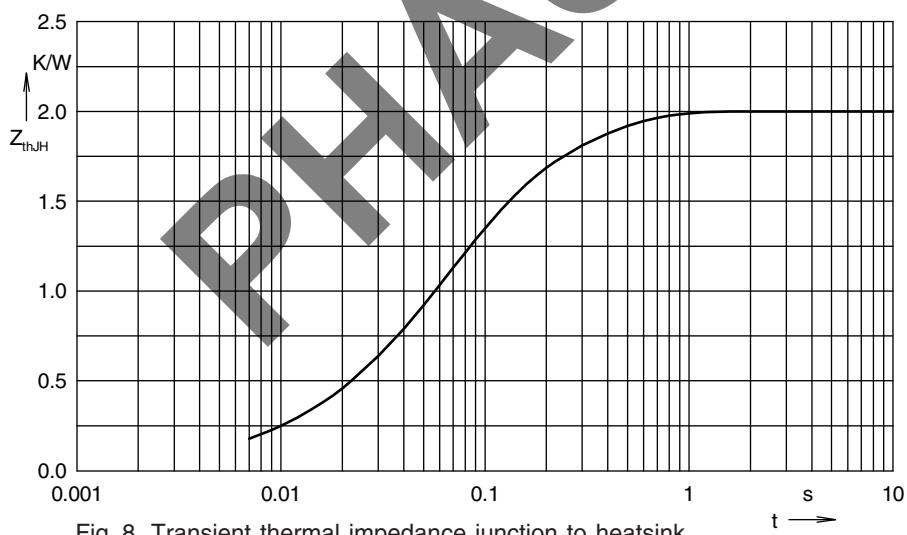


Fig. 8 Transient thermal impedance junction to heatsink

Constants for Z_{thJH} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.007	0.008
2	0.266	0.05
3	1.127	0.06
4	0.6	0.25

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